

EAST - [10691400.wsp:1]

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L1: (6) oxygen-free near silicon near carbide or oxygen near free near silicon near carbide
 L2: (1) 1 and tetramethylsilane
 L3: (6) 1 and (tetramethylsilane Torr plasma)
 L4: (36) oxygen-free with silicon adj carbide or oxygen near free near silicon near carbide
 L5: (0) ("4andtetrarmethylsilane").PH.
 L6: (3) 4 and tetramethylsilane

Section: Title: Browse: Query: Clear:
 File: US-PG-PUB:USPAT: EPO: JPO ☐ Plural:
 Default operator: OR ☒ Highlight all hit items initially
 oxygen-free with silicon adj carbide or oxygen near free near silicon near carbide

☐ BRStom ☐ IS&I form ☐ Image ☐ Text ☐ HTML

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20050009320 A1	20050113	13	Method of forming silicon carbide films	438/624		
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20040161535 A1	20040819	16	Method of forming silicon carbide films	427/249.15		
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20040137756 A1	20040715	16	METHOD OF IMPROVING STABILITY IN LOW K BARRIER LAYERS	438/776		
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20040115876 A1	20040617	30	Method of manufacturing silicon carbide film	438/200		
5	<input type="checkbox"/>	<input type="checkbox"/>	US 20040101625 A1	20040527	15	Nitrogen passivation of interface states in SiO2/SiC structures	427/378	257/E21.267; 257/E21.269	
6	<input type="checkbox"/>	<input type="checkbox"/>	US 20040067308 A1	20040408	12	Two-layer film for next generation damascene barrier application with good oxidation resistance	427/249.15	257/E21.266; 257/E21.579; 427/569	
7	<input type="checkbox"/>	<input type="checkbox"/>	US 20030194496 A1	20031016	9	Methods for depositing dielectric material	427/255.28	427/372.2; 427/569	
8	<input type="checkbox"/>	<input type="checkbox"/>	US 20030139035 A1	20030724	12	Low dielectric (low k) barrier films with oxygen doping by plasma-enhanced chemical vapor deposition (pnevd)	438/643	257/E21.261; 257/E21.277; 257/E21.579;	
9	<input type="checkbox"/>	<input type="checkbox"/>	US 20030129827 A1	20030710	18	Method of depositing dielectric materials in damascene applications	438/629	257/E21.261; 257/E21.277; 257/E21.579	
10	<input type="checkbox"/>	<input type="checkbox"/>	US 20030024902 A1	20030206	14	Method of plasma etching low-k dielectric materials	216/67	257/E21.252; 257/E21.256;	
11	<input type="checkbox"/>	<input type="checkbox"/>	US 20010022034 A1	20010920	10	Calibrating body	33/702	257/E21.579 33/502	